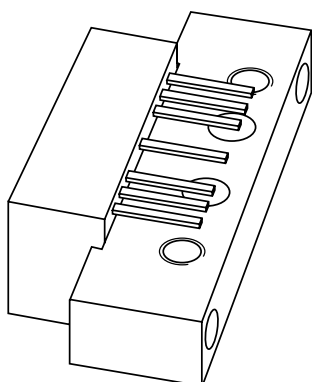


DATA SHEET



BGD702N

750 MHz, 18.5 dB gain power
doubler amplifier

Product specification
Supersedes data of 2001 Oct 25

2001 Nov 02

750 MHz, 18.5 dB gain power doubler amplifier

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FEATURES

- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

APPLICATIONS

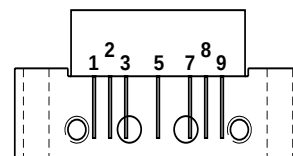
- CATV systems operating in the 40 to 750 MHz frequency range.

DESCRIPTION

Hybrid amplifier module in a SOT115J package operating at a voltage supply of 24 V (DC).

PINNING - SOT115J

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output



Side view

MSA319

Fig.1 Simplified outline.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz	18	19	dB
		f = 750 MHz	18.5	—	dB
I _{tot}	total current consumption (DC)	V _B = 24 V	—	435	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	—	65	dBmV
T _{stg}	storage temperature	−40	+100	°C
T _{mb}	operating mounting base temperature	−20	+100	°C

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CHARACTERISTICS

Table 1 Bandwidth 40 to 750 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75$ Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G_p	power gain	$f = 50$ MHz	18	19	dB
		$f = 750$ MHz	18.5	–	dB
SL	slope cable equivalent	$f = 40$ to 750 MHz	0.2	2	dB
FL	flatness of frequency response	$f = 40$ to 750 MHz	–	± 0.25	dB
S_{11}	input return losses	$f = 40$ to 80 MHz	20	–	dB
		$f = 80$ to 160 MHz	19	–	dB
		$f = 160$ to 320 MHz	18	–	dB
		$f = 320$ to 640 MHz	17	–	dB
		$f = 640$ to 750 MHz	16	–	dB
S_{22}	output return losses	$f = 40$ to 80 MHz	20	–	dB
		$f = 80$ to 160 MHz	19	–	dB
		$f = 160$ to 320 MHz	18	–	dB
		$f = 320$ to 640 MHz	17	–	dB
		$f = 640$ to 750 MHz	16	–	dB
S_{21}	phase response	$f = 50$ MHz	–45	+45	deg
CTB	composite triple beat	110 channels flat; $V_o = 44$ dBmV; measured at 745.25 MHz	–	–58	dB
X_{mod}	cross modulation	110 channels flat; $V_o = 44$ dBmV; measured at 55.25 MHz	–	–62	dB
CSO	composite second order distortion	110 channels flat; $V_o = 44$ dBmV; measured at 746.5 MHz	–	–58	dB
d_2	second order distortion	note 1	–	–68	dB
V_o	output voltage	$d_{im} = -60$ dB; note 2	61	–	dBmV
F	noise figure	$f = 50$ MHz	–	5.5	dB
		$f = 450$ MHz	–	6.5	dB
		$f = 550$ MHz	–	6.5	dB
		$f = 600$ MHz	–	7	dB
		$f = 750$ MHz	–	8.5	dB
I_{tot}	total current consumption (DC)	note 3	–	435	mA

Notes

- $f_p = 55.25$ MHz; $V_p = 44$ dBmV;
 $f_q = 691.25$ MHz; $V_q = 44$ dBmV;
measured at $f_p + f_q = 746.5$ MHz.
- Measured according to DIN45004B:
 $f_p = 740.25$ MHz; $V_p = V_o$;
 $f_q = 747.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 749.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 738.25$ MHz.
- The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 30 V.

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Table 2 Bandwidth 40 to 600 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G_p	power gain	$f = 50$ MHz	18	19	dB
		$f = 600$ MHz	18.5	–	dB
SL	slope cable equivalent	$f = 40$ to 600 MHz	0.2	2	dB
FL	flatness of frequency response	$f = 40$ to 600 MHz	–	± 0.2	dB
S_{11}	input return losses	$f = 40$ to 80 MHz	20	–	dB
		$f = 80$ to 160 MHz	19	–	dB
		$f = 160$ to 320 MHz	18	–	dB
		$f = 320$ to 600 MHz	17	–	dB
S_{22}	output return losses	$f = 40$ to 80 MHz	20	–	dB
		$f = 80$ to 160 MHz	19	–	dB
		$f = 160$ to 320 MHz	18	–	dB
		$f = 320$ to 600 MHz	17	–	dB
S_{21}	phase response	$f = 50$ MHz	–45	+45	deg
CTB	composite triple beat	85 channels flat; $V_o = 44$ dBmV; measured at 595.25 MHz	–	–65	dB
X_{mod}	cross modulation	85 channels flat; $V_o = 44$ dBmV; measured at 55.25 MHz	–	–65	dB
CSO	composite second order distortion	85 channels flat; $V_o = 44$ dBmV; measured at 596.5 MHz	–	–60	dB
d_2	second order distortion	note 1	–	–70	dB
V_o	output voltage	$d_{im} = -60$ dB; note 2	64	–	dBmV
F	noise figure	see Table 1	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	435	mA

Notes

- $f_p = 55.25$ MHz; $V_p = 44$ dBmV;
 $f_q = 541.25$ MHz; $V_q = 44$ dBmV;
measured at $f_p + f_q = 596.5$ MHz.
- Measured according to DIN45004B:
 $f_p = 590.25$ MHz; $V_p = V_o$;
 $f_q = 597.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 599.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 588.25$ MHz.
- The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 30 V.

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Table 3 Bandwidth 40 to 550 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G_p	power gain	$f = 50$ MHz	18	19	dB
		$f = 550$ MHz	18.5	–	dB
SL	slope cable equivalent	$f = 40$ to 550 MHz	0.2	2	dB
FL	flatness of frequency response	$f = 40$ to 550 MHz	–	± 0.2	dB
S_{11}	input return losses	$f = 40$ to 80 MHz	20	–	dB
		$f = 80$ to 160 MHz	19	–	dB
		$f = 160$ to 320 MHz	18	–	dB
		$f = 320$ to 550 MHz	17	–	dB
S_{22}	output return losses	$f = 40$ to 80 MHz	20	–	dB
		$f = 80$ to 160 MHz	19	–	dB
		$f = 160$ to 320 MHz	18	–	dB
		$f = 320$ to 550 MHz	17	–	dB
S_{21}	phase response	$f = 50$ MHz	–45	+45	deg
CTB	composite triple beat	77 channels flat; $V_o = 44$ dBmV; measured at 547.25 MHz	–	–67	dB
X_{mod}	cross modulation	77 channels flat; $V_o = 44$ dBmV; measured at 55.25 MHz	–	–67	dB
CSO	composite second order distortion	77 channels flat; $V_o = 44$ dBmV; measured at 548.5 MHz	–	–62	dB
d_2	second order distortion	note 1	–	–72	dB
V_o	output voltage	$d_{im} = -60$ dB; note 2	64.5	–	dBmV
F	noise figure	see Table 1	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	435	mA

Notes

- $f_p = 55.25$ MHz; $V_p = 44$ dBmV;
 $f_q = 493.25$ MHz; $V_q = 44$ dBmV;
measured at $f_p + f_q = 548.5$ MHz.
- Measured according to DIN45004B:
 $f_p = 540.25$ MHz; $V_p = V_o$;
 $f_q = 547.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 549.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 538.25$ MHz.
- The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 30 V.

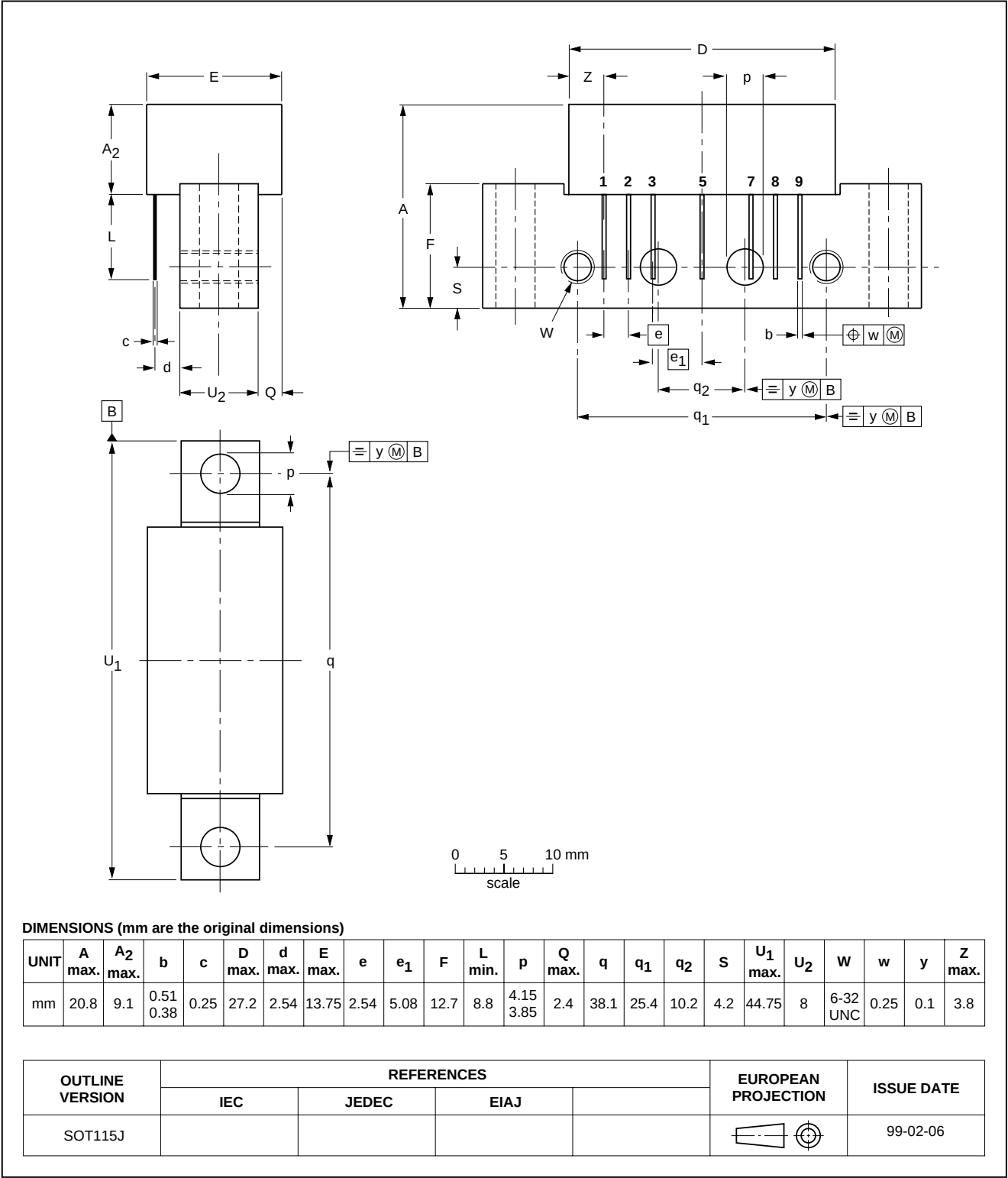
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PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes;
2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J



750 MHz, 18.5 dB gain power doubler amplifier

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